

SURFACE MOUNT ULTRA LOW LEAKAGE SILICON SWITCHING DIODES



V_R=0, f=1.0MHz

 $I_R=I_F=10mA$, $I_{rr}=1.0mA$, $R_L=100\Omega$

CT

t_{rr}

• Device is *Halogen Free* by design

Central[®] Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMSD6001 SERIES are silicon switching diodes manufactured by the epitaxial planar process, epoxy molded in a SUPERmini[™] surface mount package, designed for switching applications requiring an extremely low leakage diode.

2.0

3.0

CMSD6001	: SINGLE A: DUAL, COMMON ANODE C: DUAL, COMMON CATHODE S: DUAL, IN-SERIES	MARKING CO MARKING CO MARKING CO MARKING CO	DDE: 61A DDE: 61C				
MAXIMUM RATINGS: (T _A =25°C)		SYMBOL		UNITS			
Continuous Reverse Voltage		VR	75	V			
Peak Repetitive Reverse Voltage		V _{RRM}	100	V			
Continuous Forward Current		١ _F	250	mA			
Peak Repetitive Forward Current		IFRM	250	mA			
Peak Forward Surge Current, tp=1.0µs		IFSM	4.0	А			
Peak Forward Surge Current, tp=1.0s		IFSM	1.0	А			
Power Dissipation		PD	275	mW			
Operating and Storage Junction Temperature		т _Ј , Т _{stg}	-65 to +150	°C			
Thermal Resistance		Θ_{JA}	455	°C/W			
ELECTRICAL CHARACTERISTICS PER DIODE: (TA=25°C unless otherwise noted)							
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS			
I _R	V _R =75V		500	рА			
BVR	I _R =100μA	100		V			
V _F	I _F =1.0mA		0.85	V			
V _F	I _F =10mA		0.95	V			
VF	I _F =100mA		1.1	V			

R3 (9-May 2011)

pF

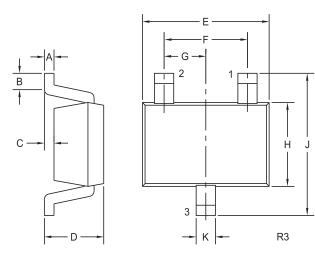
μs





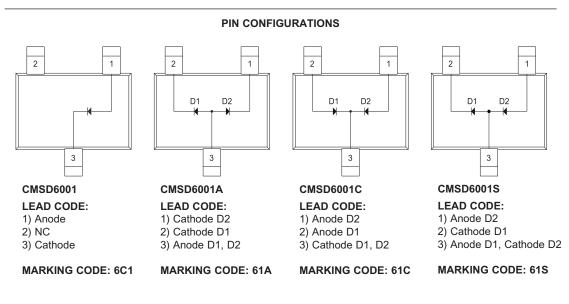
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SOT-323 CASE - MECHANICAL OUTLINE



DIMENSIONS							
	INCHES		MILLIMETERS				
SYMBOL	MIN	MAX	MIN	MAX			
А	0.002	0.008	0.05	0.20			
В	0.004	-	0.10	-			
С	-	0.004	-	0.10			
D	0.031	0.043	0.80	1.10			
E	0.071	0.087	1.80	2.20			
F	0.051		1.30				
G	0.026		0.65				
Н	0.045	0.053	1.15	1.35			
J	0.079	0.087	2.00	2.20			
K	0.008	0.016	0.20	0.40			
SOT-323 (REV/· R3)							

SOT-323 (REV: R3)



R3 (9-May 2011)

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